

**Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/660,559 on January 12, 2005**

**Combined Classifications**

5 257/192	2 257/E29.14
5 257/E29.268	2 257/E29.175
4 257/488	2 257/E29.19
4 257/E21.387	2 257/E29.252
4 257/E21.625	2 257/E29.257
4 257/E21.639	2 257/E29.258
4 257/E29.114	2 257/E29.26
3 257/339	2 438/227
3 257/587	2 438/238
3 257/77	2 438/286
3 257/E21.375	2 438/297
3 257/E23.019	2 438/298
3 257/E29.051	2 438/305
3 257/E29.064	2 438/307
3 257/E29.185	2 438/384
3 257/E29.189	
3 257/E29.253	
3 257/E29.256	
3 438/586	
2 257/194	
2 257/197	
2 257/289	
2 257/290	
2 257/341	
2 257/344	
2 257/345	
2 257/399	
2 257/408	
2 257/409	
2 257/491	
2 257/495	
2 257/518	
2 257/577	
2 257/750	
2 257/758	
2 257/E21.086	
2 257/E21.167	
2 257/E21.407	
2 257/E21.418	
2 257/E21.419	
2 257/E21.576	
2 257/E21.593	
2 257/E21.696	
2 257/E23.164	
2 257/E27.012	
2 257/E29.01	
2 257/E29.013	
2 257/E29.03	
2 257/E29.104	
2 257/E29.124	

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Titles of Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/660,559 on January 12, 2005

5 257/192 (4 OR, 1 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/183 HETEROJUNCTION DEVICE

257/192 .Field effect transistor

4 257/488 (1 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/487 WITH MEANS TO INCREASE BREAKDOWN VOLTAGE  
THRESHOLD

257/488 .Field relief electrode

3 257/339 (1 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of 10 15 cm<sup>-3</sup> or less)

257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)

257/327 ..Short channel insulated gate field effect  
transistor

257/335 ...Active channel region has a graded dopant  
concentration decreasing with distance from source region  
(e.g., double diffused device, DMOS transistor)

257/339 ....With means to increase breakdown voltage

3 257/587 (0 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/565 BIPOLAR TRANSISTOR STRUCTURE

257/587 .With specified electrode means

3 257/77 (1 OR, 2 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/76 SPECIFIED WIDE BAND GAP (1.5eV) SEMICONDUCTOR  
MATERIAL OTHER THAN GaAsP or GaAlAs

257/77 .Diamond or silicon carbide

**PLUS Search Results for S/N 10/660,.559, Searched January 12, 2005 (Top 50)**

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

5831292	5650658	4528744	4893157	5191402
4929991	5885878	4583105	4914491	5221856
4990990	5932894	4593152	4918026	5258631
5701026	5972759	4608696	4924288	5345101
5726069	6121684	4764801	4929992	5345103
6104043	4253105	4784968	4965650	5381027
6147371	4314269	4819044	4972237	5381031
5322804	4319257	4835592	4980748	5382814
5541435	4348746	4857479	5008719	5434435
5622878	4486770	4866491	5187122	5471232